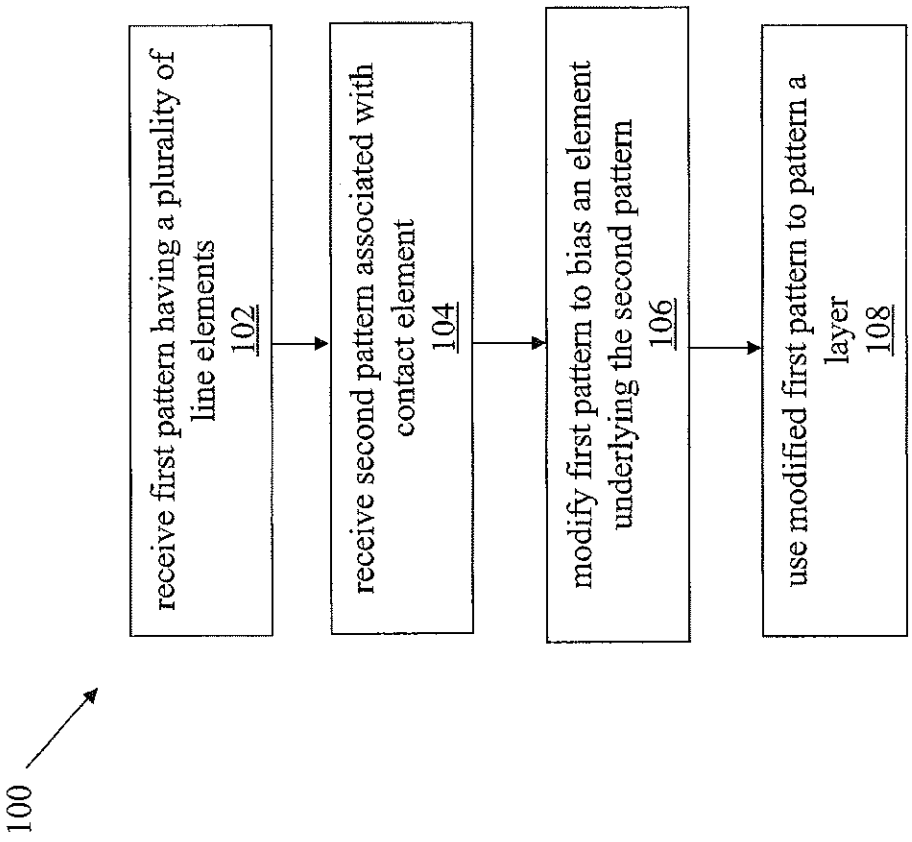

100
receive first pattern having a plurality of line elements
102
receive second pattern associated with contact element
104
modify first pattern to bias an element underlying the second pattern
106
use modified first pattern to pattern a layer
108

Fig. 1

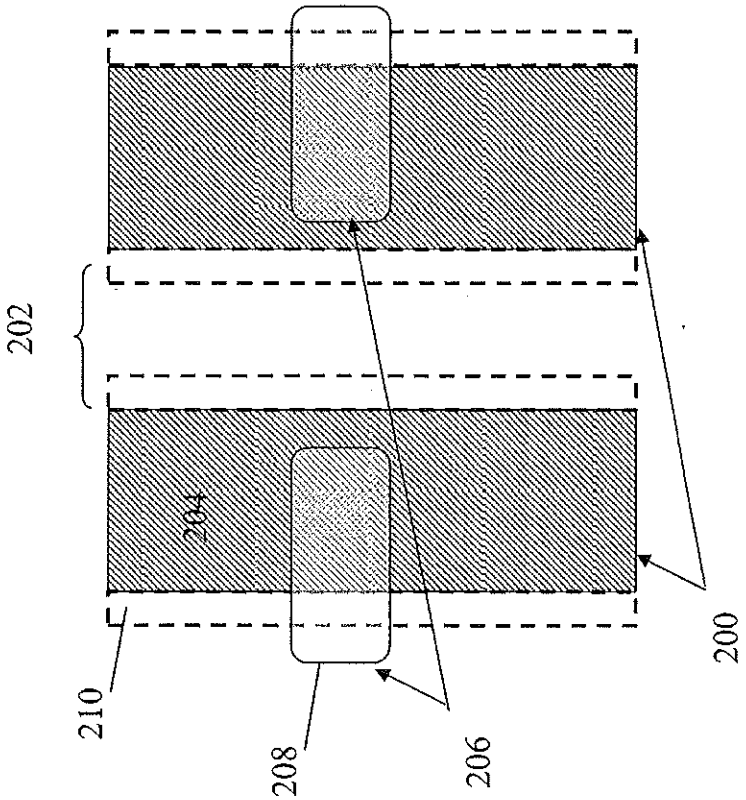


Fig. 2

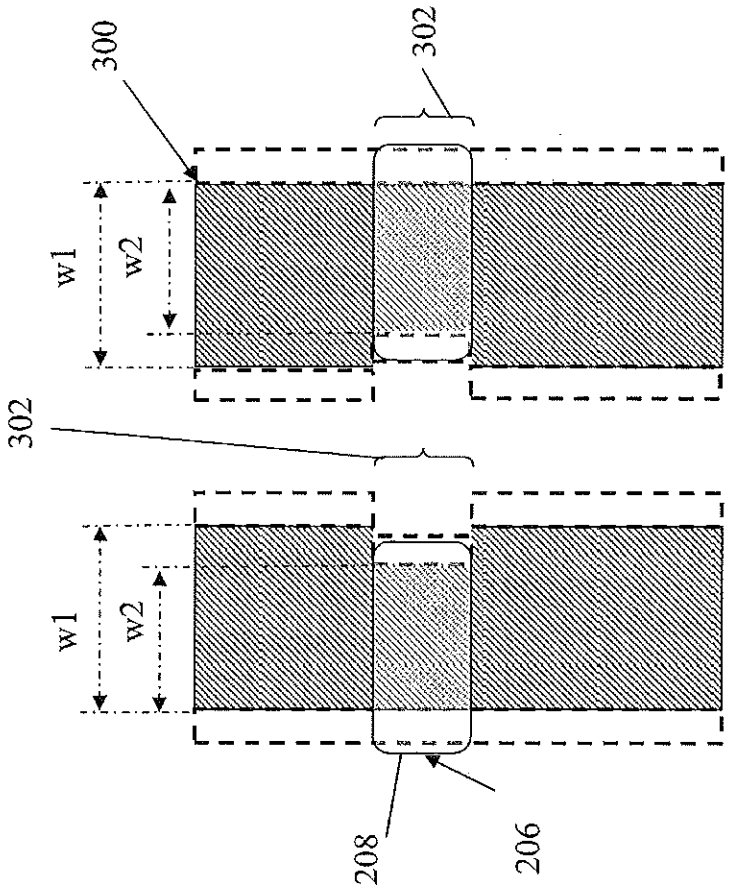


Fig. 3

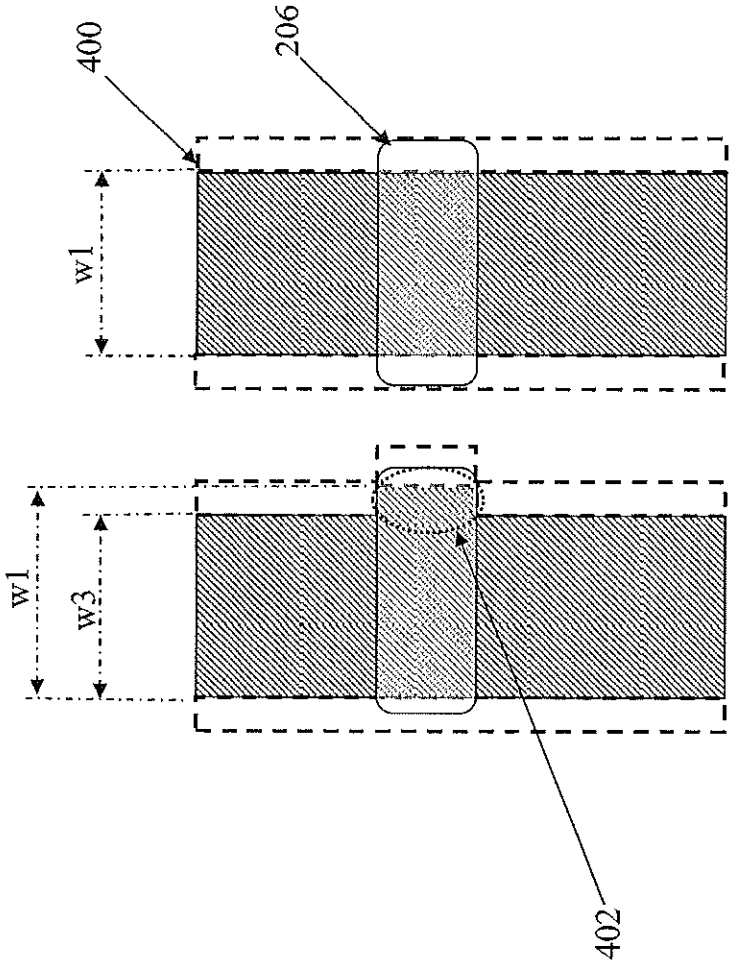


Fig. 4

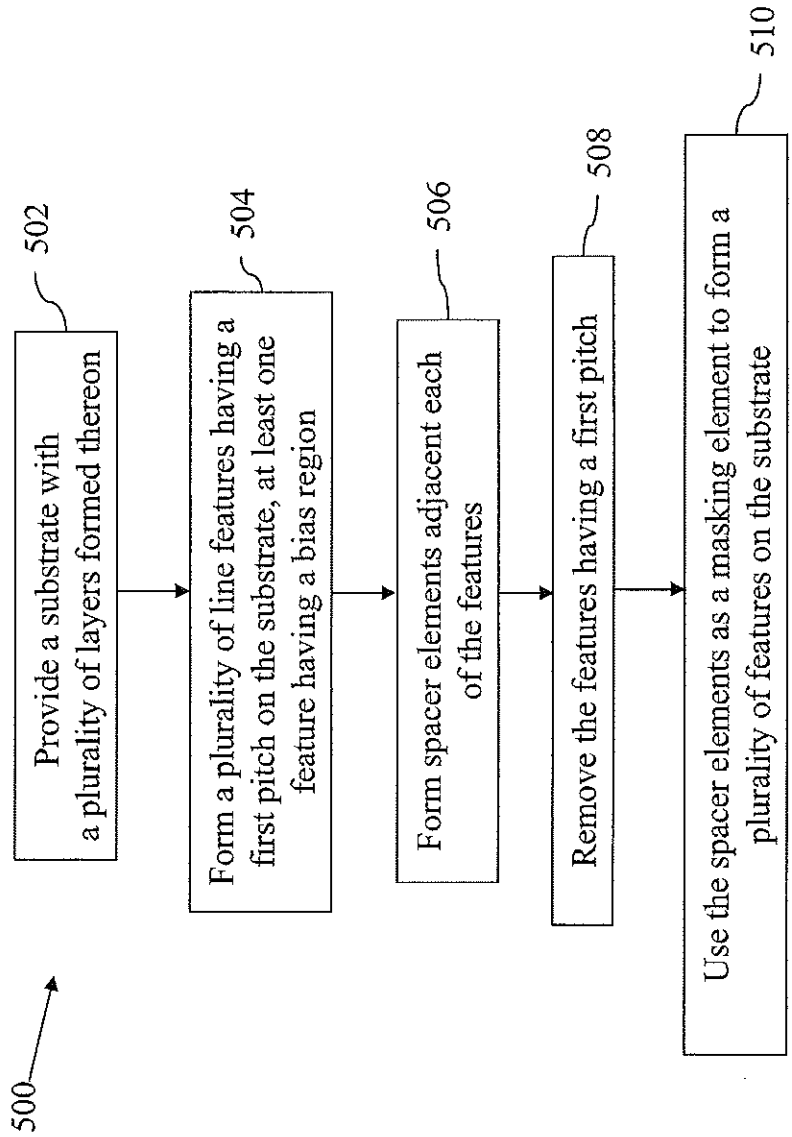

500
Provide a substrate with a plurality of layers formed thereon
502
Form a plurality of line features having a first pitch on the substrate, at least one feature having a bias region
504
Form spacer elements adjacent each of the features
506
Remove the features having a first pitch
508
Use the spacer elements as a masking element to form a plurality of features on the substrate
510

Fig. 5

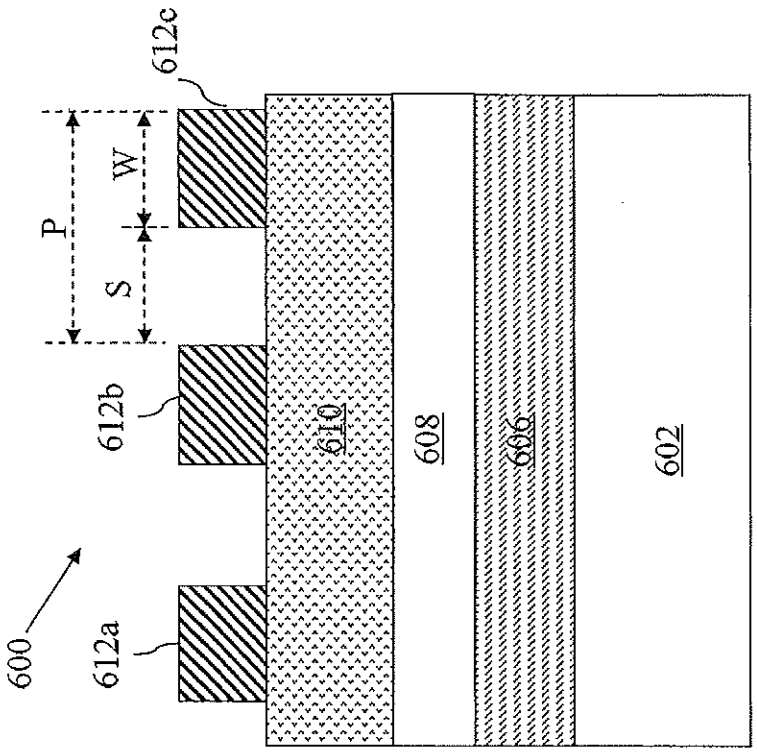


Fig. 6a

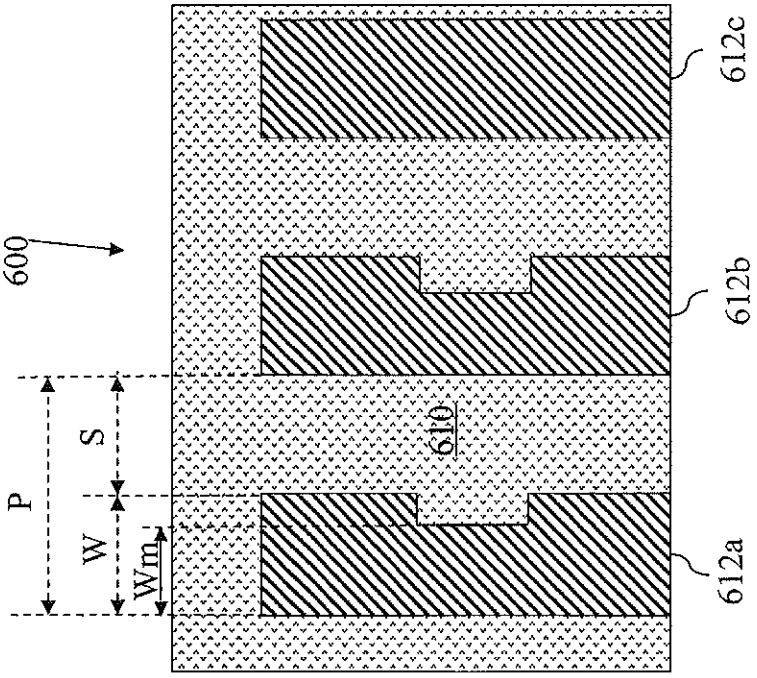


Fig. 6b

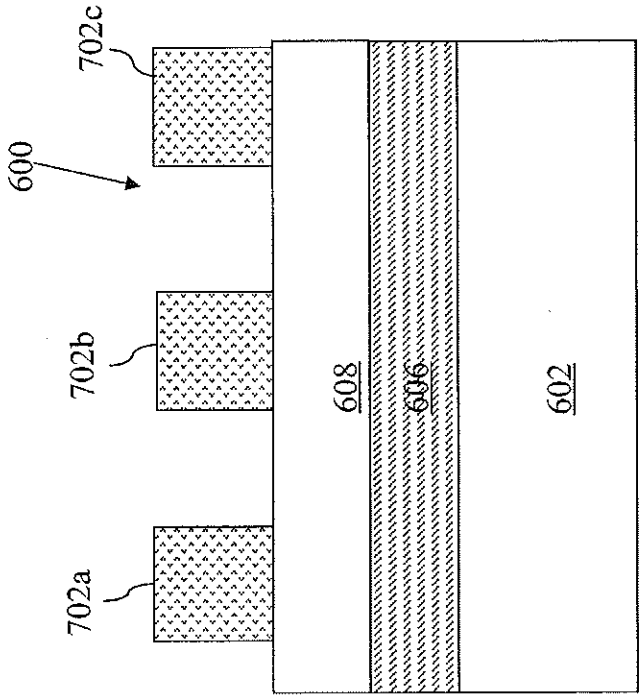


Fig. 7a

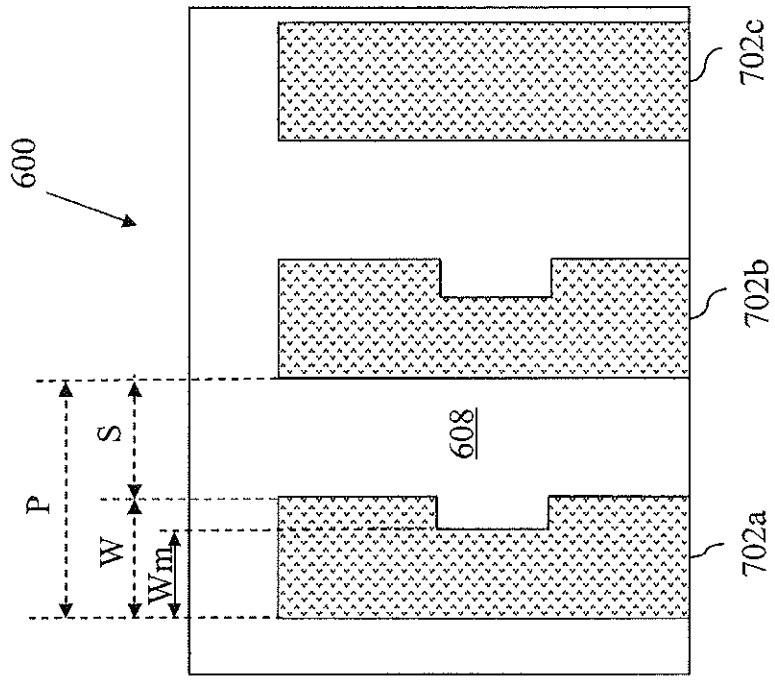


Fig. 7b

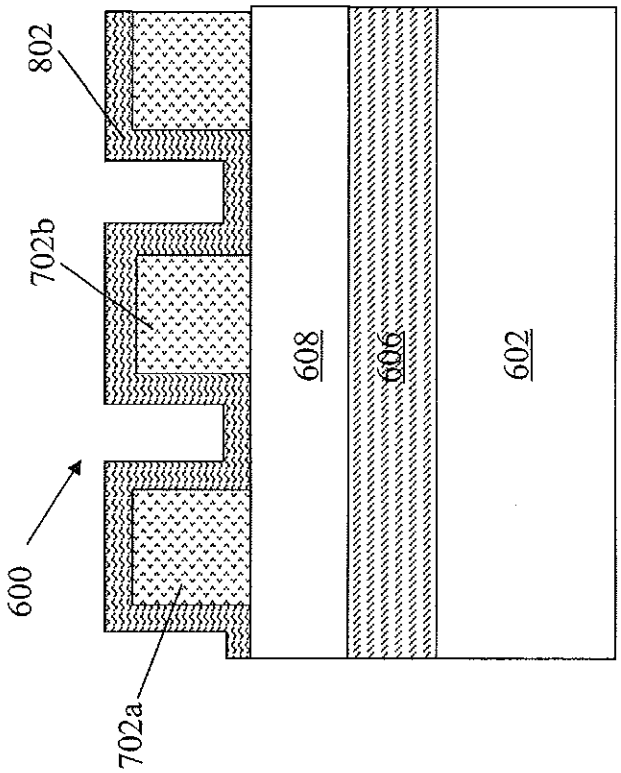


Fig. 8a

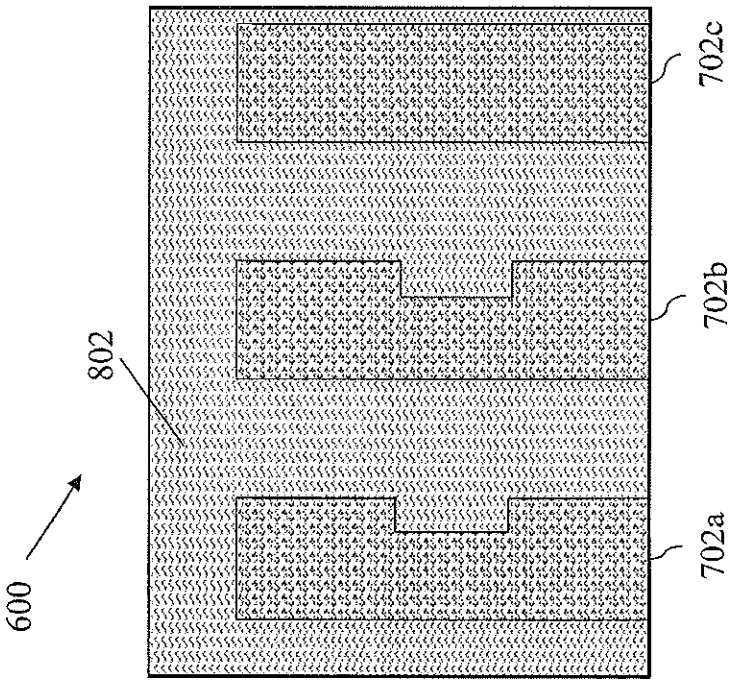


Fig. 8b

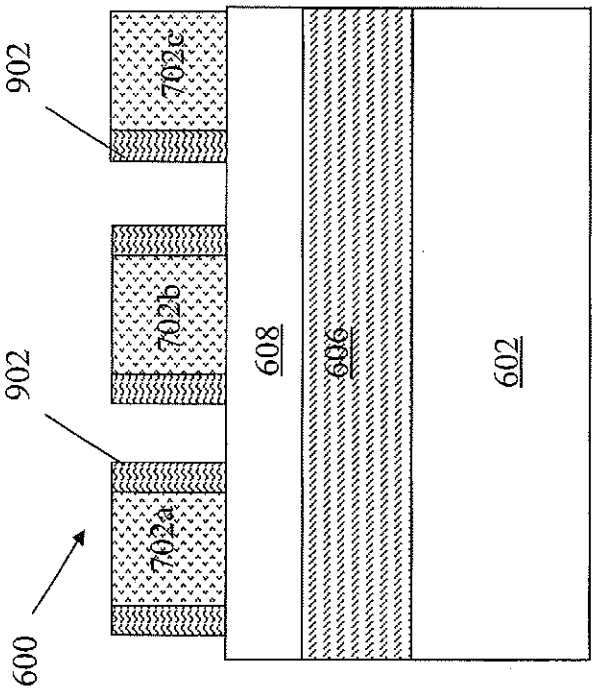


Fig. 9a

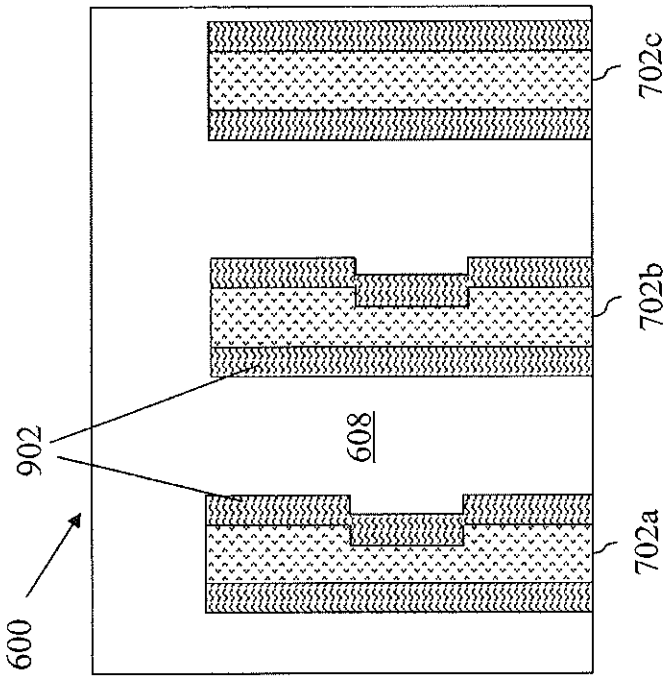


Fig. 9b

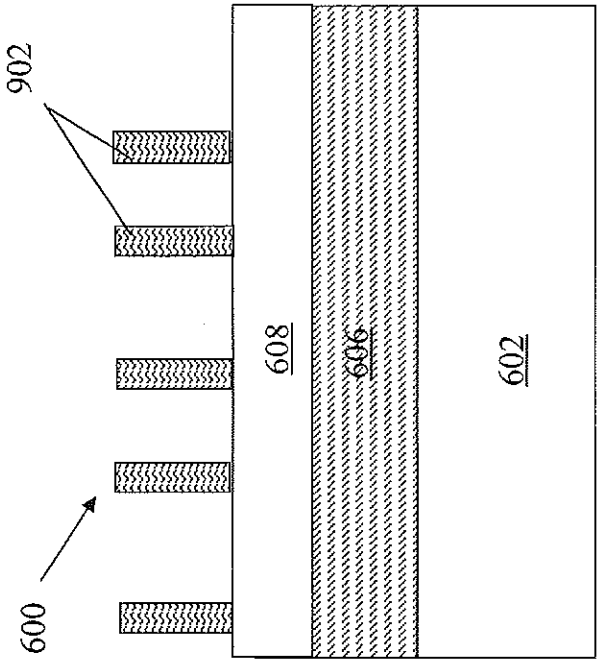


Fig. 10a

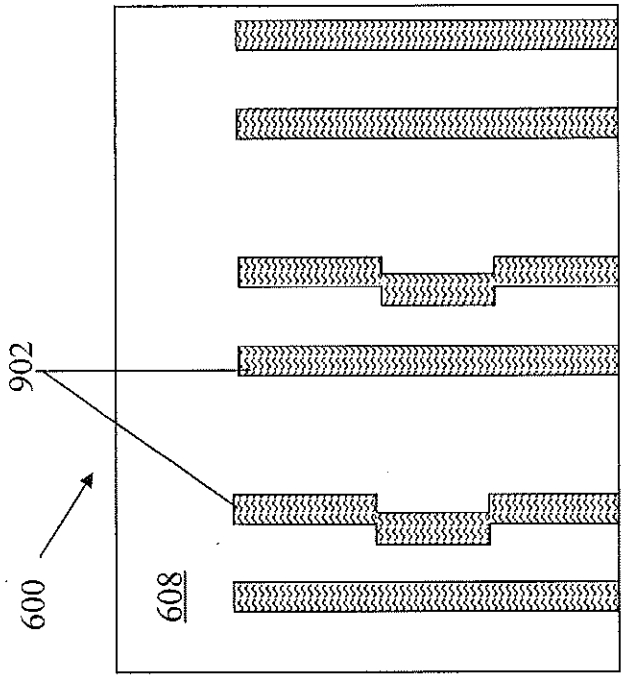


Fig. 10b

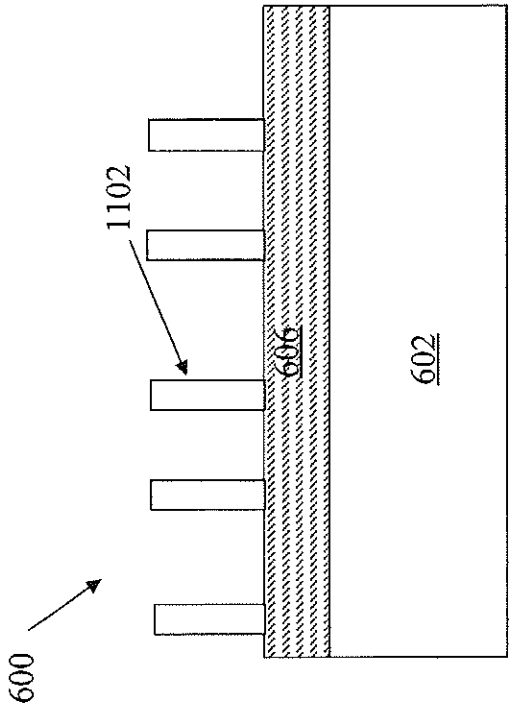


Fig. 11a

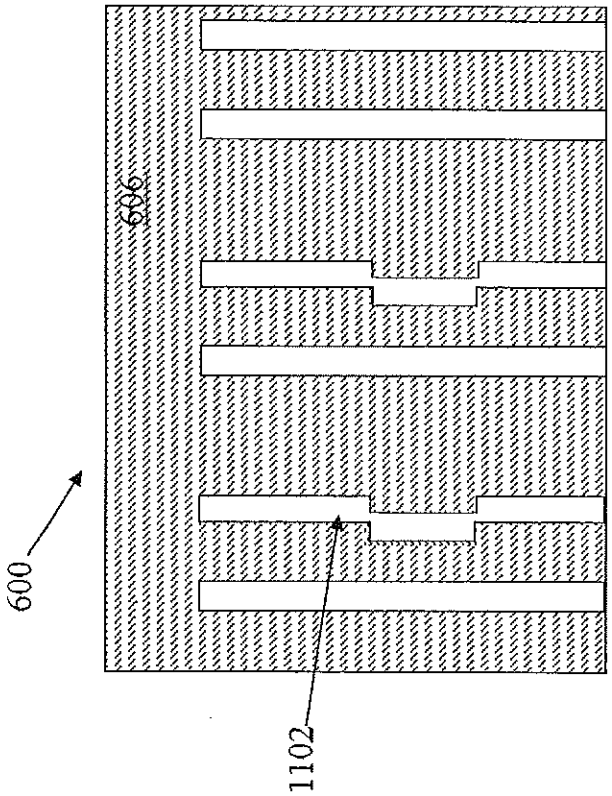


Fig. 11b

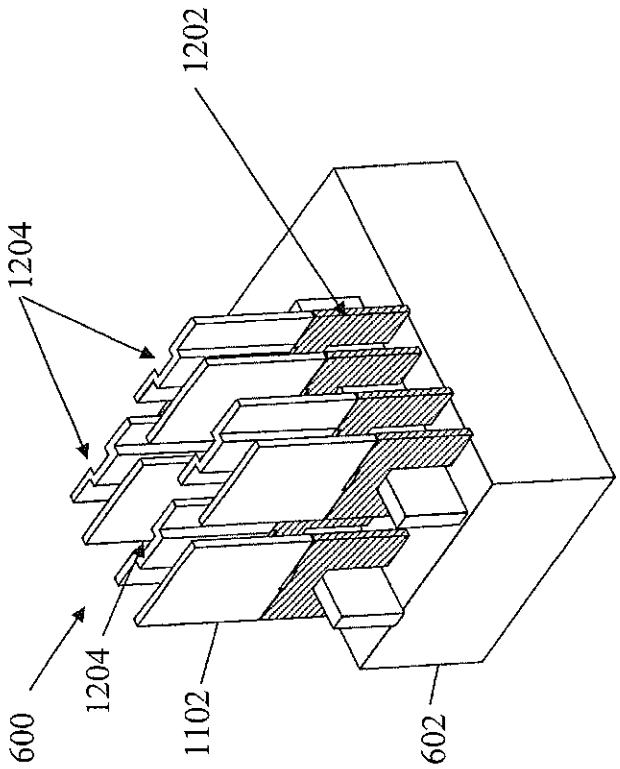


Fig. 12

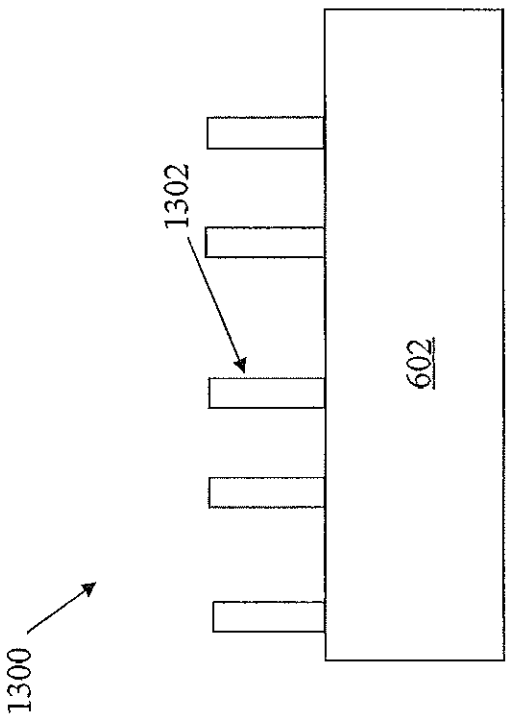


Fig. 13a

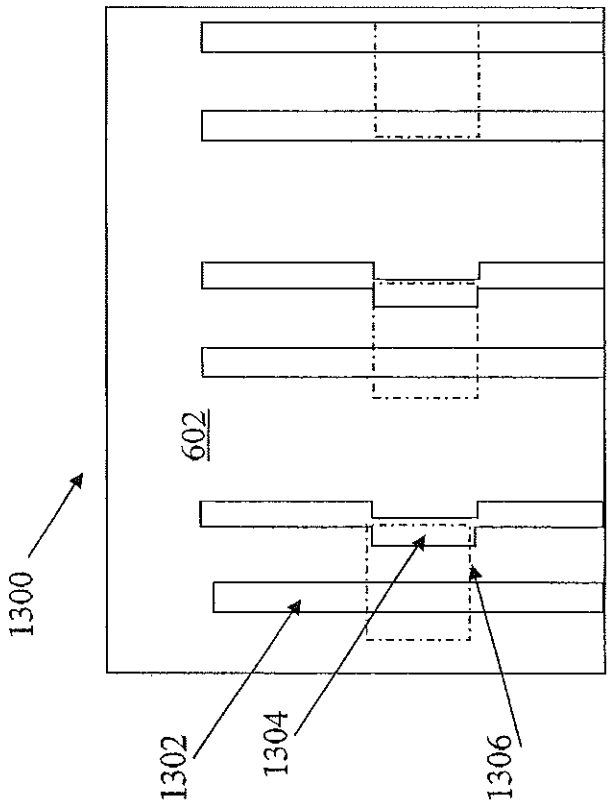


Fig. 13b

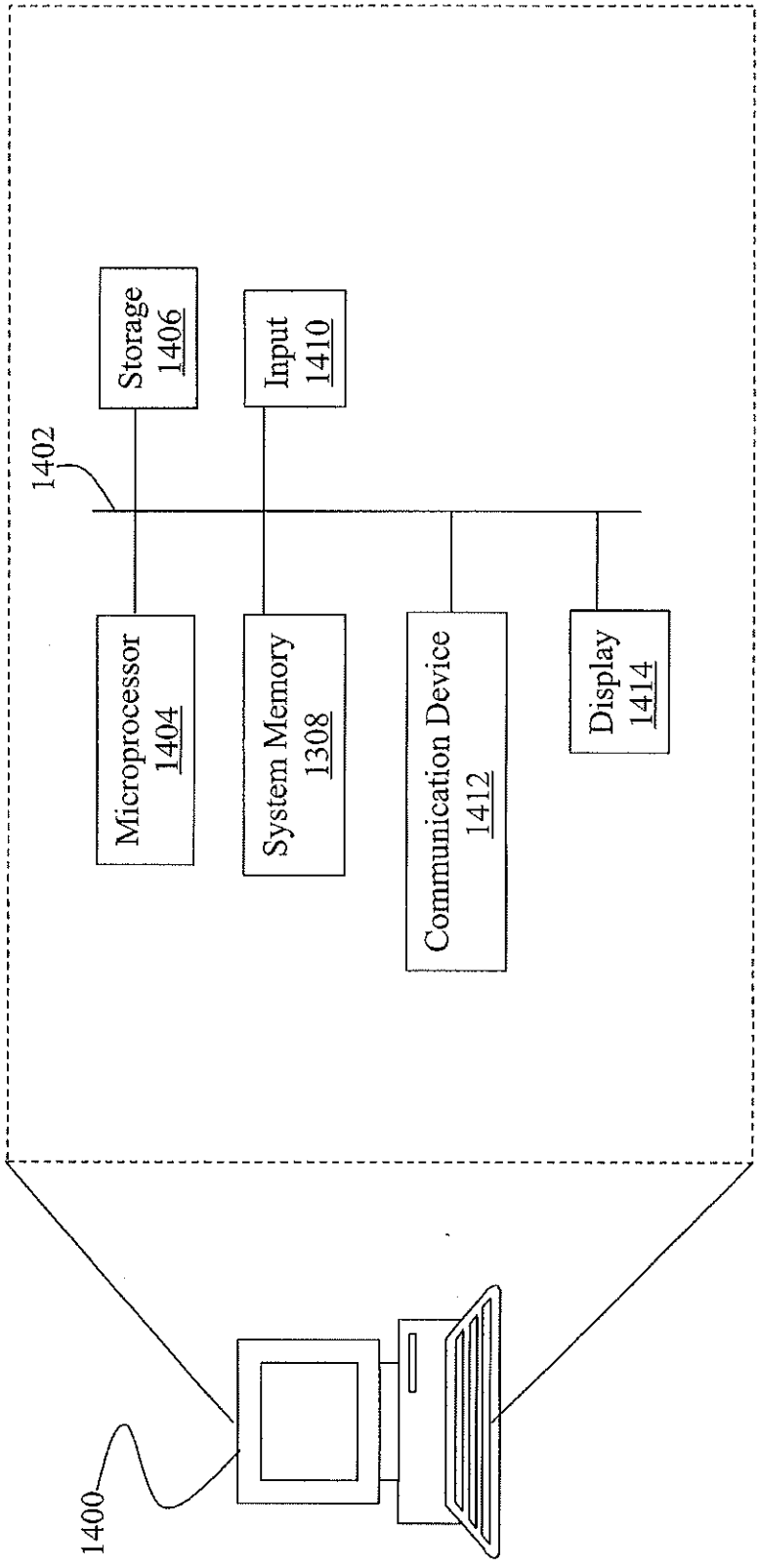

1400
1402
Storage 1406
Input 1410
Microprocessor 1404
System Memory 1308
Communication Device 1412
Display 1414

Fig. 14